	Application No.	Applicant(s)	
Notice of Allowability	09/782,441	LAI ET AL.	
Motive of Anowability	Examiner	Art Unit	
	Tuan Quach	2814	
The MAILING DATE of this communication app of All claims being allowable, PROSECUTION ON THE MERITS IS (herewith (or previously mailed), a Notice of Allowance (PTOL-85) NOTICE OF ALLOWABILITY IS NOT A GRANT OF PATENT RICO of the Office or upon petition by the applicant. See 37 CFR 1.313	or other appropriate commu GHTS. This application is s and MPEP 1308.	th the correspondence address-	e. <b>THIS</b> ne initiativ
1. This communication is responsive to communication filed Fe	ebruary 17, 2004.		
2. The allowed claim(s) is/are <u>13-16,42-48 and 52-58</u> .			,
3. The drawings filed on 13 February 2001 are accepted by the	e Examiner		·
4. ☐ Acknowledgment is made of a claim for foreign priority und a) ☐ All b) ☐ Some* c) ☐ None of the:	der 35 U.S.C. § 119(a)-(d) o	or (f).	·
Certified copies of the priority documents have be     Certified copies of the priority documents.	peen received.	•	
2. Certified copies of the priority documents have b	een received in Application	ı No	,
3. Copies of the certified copies of the priority docu	ments have been received	in this national stage application fro	m the
international buleau (FC) Rule 17.2(a)).		=	-
* Certified copies not received:		•	
Applicant has THREE MONTHS FROM THE "MAILING DATE" of noted below. Failure to timely comply will result in ABANDONMEI THIS THREE-MONTH PERIOD IS NOT EXTENDABLE.	itt of this application.		
5. A SUBSTITUTE OATH OR DECLARATION must be submitted INFORMAL PATENT APPLICATION (PTO-152) which gives	reason(s) why the bath or o	MINER'S AMENDMENT or NOTICE declaration is deficient.	OF
6. CORRECTED DRAWINGS (as "replacement sheets") must be	pe submitted.		
(a) Including changes required by the Notice of Draftsperson	r's Patent Drawing Review	( PTO-948) attached	·•·
i) Li riereto or 2) Li to Paper No./Mail Date		•	
(b) ☐ including changes required by the attached Examiner's A Paper No./Mail Date	mendment / Comment or in	the Office action of	
Identifying indicia such as the application number (see 37 CFR 1.84(each sheet. Replacement sheet(s) should be labeled as such in the	(c)) should be written on the	drawings in the front (not the back) o	Æ
<ol> <li>DEPOSIT OF and/or INFORMATION about the deposit attached Examiner's comment regarding REQUIREMENT FO</li> </ol>	OF BIOLOGICAL MATER R THE DEPOSIT OF BIOL	₹IAL must be submitted. Note the OGICAL MATERIAL	
			•
	•	exe	
Attachment(s)	•		
Notice of References Cited (PTO-892)			
P. ☐ Notice of Draftperson's Patent Drawing Review (PTO-948)	5. Notice of Inform	mal Patent Application (PTO-152)	
	6.	mary (PTO-413).	
☐ Information Disclosure Statements (PTO-1449 or PTO/SB/08), Paper No./Mail Date	Paper No./Ma 7. ☐ Examiner's Am	ail Datenendment/Comment	
Examiner's Comment Regarding Requirement for Deposit	8. 🛛 Examiner's Sta	atement of Reasons for Allowance	
of Biological Material	9. ☑ Other <u>Copy of</u>	Comm. Related Appl.	
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Application/Control Number: 09/782,441

Art Unit: 2814

## **REASONS FOR ALLOWANCE**

The following is an examiner's statement of reasons for allowance:

Claims 13-16 and 42-48 are allowed primarily because the prior art do not teach or suggest the claimed limitations as delineated in claims 13 and 42 regarding a method of fabricating an interconnect comprising flowing a first titanium-containing precursor in the chemical vapor deposition reaction chamber, flowing nitrogen in the chemical vapor deposition reaction chamber simultaneously with the flowing the titanium-containing precursor to form a first layer of titanium nitride on the semiconductor structure, flowing a second titanium-containing precursor, flowing at least one gas selected from ammonia and nitrogen trifluoride simulataneously to form a second layer of titanium nitride on the first titanium nitride wherein the second titanium nitride comprises a polycrystalline orientation that comprises a mixture of 1:1 of <111> and <200> oriented grains, and flowing an aluminum-containing precursor in the chamber to form an aluminum film having small grain size. Claims 52-58 are allowed primarily because the prior art do not teach or suggest exposing the semiconductor structure to a titanium-containing precursor gas and nitrogen at the respective flowrates and forming a titanium nitride thereon, exposing the semiconductor with the titanium nitride film to a titaniumcontaining precursor gas and to ammonia or nitrogen trifluoride at the claimed flow rates and forming a second titanium nitride film having a polycrystalline orientation wherein the second titanium nitride comprises a polycrystalline orientation that comprises a mixture of 1:1 of <111> and <200> oriented grains, and exposing the structure with the second titanium nitride film having a polycrystalline orientation to an aluminumcontaining organometallic precursor to from an aluminum interconnect where the aluminum has small grain size.

Any comments considered necessary by applicant must be submitted no later than the payment of the issue fee and, to avoid processing delays, should preferably accompany the issue fee. Such submissions should be clearly labeled "Comments on Statement of Reasons for Allowance."

Any inquiry concerning this communication or earlier communications from the examiner should be directed to examiner Quach whose telephone number (571)272-1717. The examiner can normally be reached on M - F from 7 to 4.

If attempts to reach the examiner by telephone are unsuccessful, the examiner's supervisor Wael Fahmy can be reached on (571)272-1705. The fax phone number for the organization where this application or proceeding is assigned is (703)872-9306.

Any inquiry of a general nature or relating to the status of this application or proceeding should be directed to the receptionist whose telephone number is (571)272-1562.

(二日日日日)
Tuan Quach

Primary Examiner